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TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

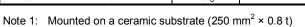
2SC2881

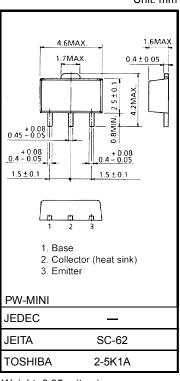
Voltage Amplifier Applications Power Amplifier Applications

- High voltage: VCEO = 120 V
- High transition frequency: $f_T = 120 \text{ MHz}$ (typ.)
- Small flat package
- $P_C = 1.0$ to 2.0 W (mounted on ceramic substrate)
- Complementary to 2SA1201

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	120	V	
Collector-emitter voltage	V _{CEO}	120	V	
Emitter-base voltage	V _{EBO}	5	V	
Collector current	۱ _C	800	mA	
Base current	Ι _Β	160	mA	
Collector power dissipation	P _C	500	mW	
	P _C	1000		
	(Note 1)	1000		
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	





Weight: 0.05 g (typ.)

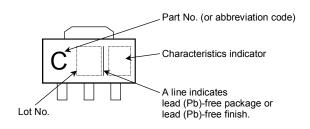
Unit: mm

Electrical Characteristics (Ta = 25°C)

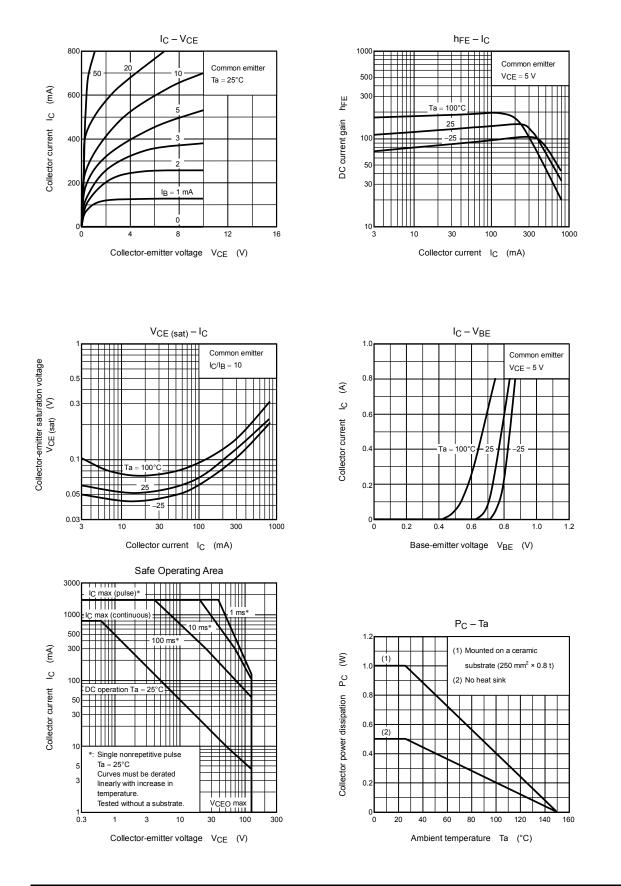
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 120 V, I _E = 0	_	_	0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.1	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	120	_	_	V
Emitter-base breakdown voltage	V _{(BR) EBO}	I _E = 1 mA, I _C = 0	5	_	_	V
DC current gain	h _{FE} (Note 2)	V _{CE} = 5 V, I _C = 100 mA	80	-	240	_
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 500 mA, I _B = 50 mA	_	_	1.0	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 500 mA	_	_	1.0	V
Transition frequency	fT	V _{CE} = 5 V, I _C = 100 mA	_	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	_	30	pF

Note 2: hFE classification O: 80 to 160, Y: 120 to 240

Marking



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